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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

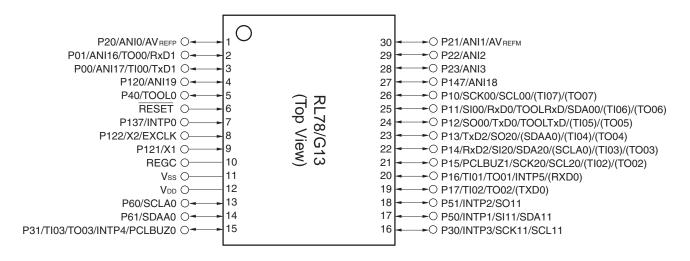
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	38
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	52-LQFP
Supplier Device Package	52-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100jlafa-v0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

## 1.3.4 30-pin products

• 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F).

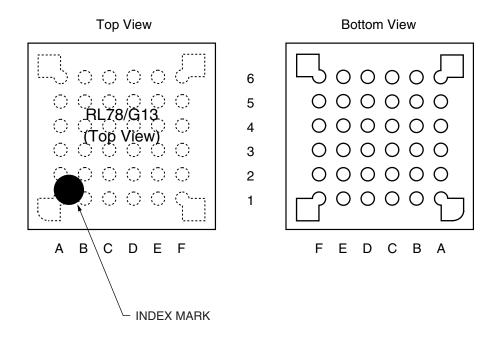
Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



## 1.3.6 36-pin products

• 36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)



	А	В	С	D	E	F	_
	P60/SCLA0	Vdd	P121/X1	P122/X2/EXCLK	P137/INTP0	P40/TOOL0	
6							6
	P62	P61/SDAA0	Vss	REGC	RESET	P120/ANI19	
5							5
4	P72/SO21	P71/SI21/ SDA21	P14/RxD2/SI20/ SDA20/(SCLA0) /(TI03)/(TO03)	P31/TI03/TO03/ INTP4/ PCLBUZ0	P00/TI00/TxD1	P01/TO00/RxD1	4
3	P50/INTP1/ SI11/SDA11	P70/SCK21/ SCL21	P15/PCLBUZ1/ SCK20/SCL20/ (TI02)/(TO02)	P22/ANI2	P20/ANI0/ AVrefp	P21/ANI1/ AVREFM	3
2	P30/INTP3/ SCK11/SCL11	P16/TI01/TO01/ INTP5/(RxD0)	P12/SO00/ TxD0/TOOLTxD /(TI05)/(TO05)	P11/SI00/RxD0/ TOOLRxD/ SDA00/(TI06)/ (TO06)	P24/ANI4	P23/ANI3	2
1	P51/INTP2/ SO11	P17/TI02/TO02/ (TxD0)	P13/TxD2/ SO20/(SDAA0)/ (TI04)/(TO04)	P10/SCK00/ SCL00/(TI07)/ (TO07)	P147/ANI18	P25/ANI5	1
	А	В	С	D	E	F	

#### Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 $\mu$ F).

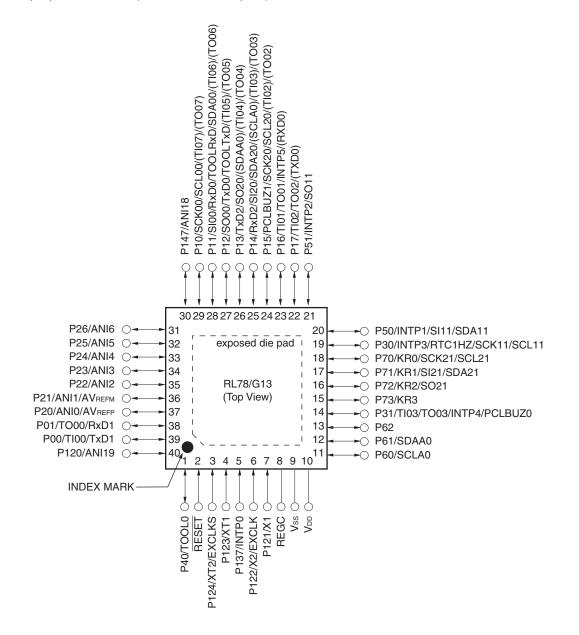
Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



## 1.3.7 40-pin products

• 40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)



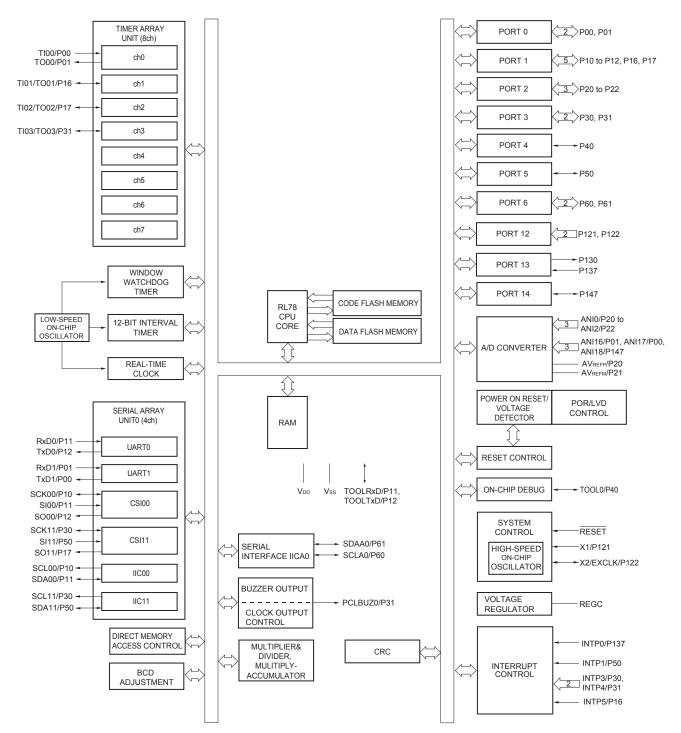


Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.
- 3. It is recommended to connect an exposed die pad to  $V_{ss.}$



## 1.5.3 25-pin products





[40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]

#### Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

	lt a sa	40				40		50		(1/2	/
	Item	40-		44-	pin		pin	52-	pin	64-	pin
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx
Code flash m	nemory (KB)	16 to	o 192	16 t	o 512	16 t	o 512	32 to	o 512	32 to	512
Data flash m	emory (KB)	4 to 8	_	4 to 8	-	4 to 8	_	4 to 8	_	4 to 8	-
RAM (KB)		2 to 1	16 <sup>Note1</sup>	2 to 3	32 <sup>Note1</sup>	2 to 3	32 <sup>Note1</sup>	2 to 3	32 <sup>Note1</sup>	2 to 3	2 <sup>Note1</sup>
Address spa	ce	1 MB									
Main system clock	High-speed system clock	HS (High HS (High LS (Low-	-speed m -speed m speed ma	c) oscillatio ain) mode ain) mode in) mode: ain) mode	1 to 20 l 1 to 16 l 1 to 8 M	MHz (Vdd = MHz (Vdd = Hz (Vdd =	= 2.7 to 5. = 2.4 to 5. 1.8 to 5.5	5 V), V),	CLK)		
	High-speed on-chip oscillator	HS (High LS (Low-	-speed m speed ma	ain) mode ain) mode in) mode: ain) mode	1 to 16 M 1 to 8 M	MHz (Vdd = Hz (Vdd =	= 2.4 to 5.5 1.8 to 5.5	5 V), V),			
Subsystem c	lock	XT1 (crys 32.768 k	,	ation, exte	rnal subsy	/stem cloc	k input (E)	KCLKS)			
Low-speed o	n-chip oscillator	15 kHz (	ΓYP.)								
General-purp	oose registers	(8-bit reg	ister $\times$ 8)	× 4 banks							
Minimum ins	truction execution time	0.03125	$\mu$ s (High-s	speed on-o	hip oscilla	ator: fін = 3	2 MHz op	eration)			
		0.05 <i>μ</i> s (	High-spee	ed system	clock: f <sub>MX</sub>	= 20 MHz	operation)				
		30.5 μs (	Subsyster	n clock: fs	ив = 32.76	8 kHz ope	ration)				
Instruction se	et	<ul><li>Adder</li><li>Multipl</li></ul>	ication (8	actor/logic bits $\times$ 8 bit	s)			and Boole	ean opera	tion), etc.	
I/O port	Total	0	36	4	10	4	14	2	18	5	8
	CMOS I/O	(N-ch ( [V <sub>DD</sub> wi	28 D.D. I/O ithstand je]: 10)	(N-ch ( [V <sub>DD</sub> w	31 D.D. I/O ithstand je]: 10)	(N-ch ( [V <sub>DD</sub> w	34 D.D. I/O ithstand je]: 11)	(N-ch ( [V <sub>DD</sub> wi	38 D.D. I/O ithstand je]: 13)	4 (N-ch C [V₀₀ wit voltag	D.D. I/C thstanc
	CMOS input		5		5		5		5	5	5
	CMOS output				_		1		1	1	1
	N-ch O.D. I/O (withstand voltage: 6 V)	:	3		4		4		4	4	1
Timer	16-bit timer					8 cha	nnels				
	Watchdog timer					1 cha	annel				
	Real-time clock (RTC)					1 cha	annel				
	12-bit interval timer (IT)						annel				
	Timer output	4 channels (PWM       5 channels (PWM outputs: 4 Note 2), outputs: 3 Note 2), 8 channels (PWM       8 channels (PWM outputs: 7 Note 2)       8 channels (PWM         0 utputs: 7 Note 2)       Note 2)       Note 2)       Note 2)         8 channels (PWM       0 utputs: 7 Note 2)       Note 2)       Note 2)									
	RTC output	1 channe • 1 Hz (s		i clock: fsu	B = 32 768	kHz)					

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = E to G, J, L): Start address FF300H

- R5F100xE, R5F101xE (x = E to G, J, L): Start address FEF00H
- R5F100xJ, R5F101xJ (x = F, G, J, L): Start address FAF00H
  - Start address F7F00H

R5F100xL, R5F101xL (x = F, G, J, L): For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944).



 The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/G13 User's Manual).

						1	(2/2)		
Ite	m	80-pin		100			3-pin		
		R5F100Mx R5	F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx		
Clock output/buzz	er output	2		:	2		2		
		<ul> <li>2.44 kHz, 4.88 kHz (Main system clock)</li> <li>256 Hz, 512 Hz, 1.0 (Subsystem clock):</li> </ul>	: fmain = 20 024 kHz, 2.	MHz operation) .048 kHz, 4.096 k	Hz, 8.192 kHz, 1		68 kHz		
8/10-bit resolution	A/D converter	17 channels		20 channels		26 channels			
Serial interface		[80-pin, 100-pin, 128-	pin product	ts]					
		<ul> <li>CSI: 2 channels/sin</li> </ul>	nplified I <sup>2</sup> C: nplified I <sup>2</sup> C:	2 channels/UAR 2 channels/UAR	T: 1 channel T (UART suppor	ting LIN-bus): 1 c	channel		
	l <sup>2</sup> C bus	2 channels		2 channels		2 channels			
Multiplier and divid	der/multiply-	• 16 bits × 16 bits = 32 bits (Unsigned or signed)							
accumulator		• 32 bits ÷ 32 bits = 32	2 bits (Unsi	igned)					
		• 16 bits × 16 bits + 32	2 bits = 32	bits (Unsigned or	signed)				
DMA controller		4 channels							
Vectored	Internal	37		3	37	41			
interrupt sources	External	13		1	3	-	13		
Key interrupt	I	8		4	8		8		
Reset		Reset by RESET pi     Internal reset by wa     Internal reset by po     Internal reset by vo     Internal reset by ille     Internal reset by RA     Internal reset by ille	ttchdog tim wer-on-res Itage detec gal instruct	et tor tion execution <sup>№te</sup> rror					
Power-on-reset ci	rcuit	<ul><li>Power-on-reset:</li><li>Power-down-reset:</li></ul>	1.51 V (TY 1.50 V (TY	,					
Voltage detector		0 0		.06 V (14 stages) 8.98 V (14 stages)					
On-chip debug fur	nction	Provided							
Power supply volta	age	$V_{DD} = 1.6 \text{ to } 5.5 \text{ V} (T_{A} = V_{DD} = 2.4 \text{ to } 5.5 \text{ V} (T_{A} = 0.25 \text{ V} )$							
Operating ambien	t temperature		$T_A = 40$ to +85°C (A: Consumer applications, D: Industrial applications ) $T_A = 40$ to +105°C (G: Industrial applications)						

<R>

**Note** The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.



## (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

# $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ (1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	HS (high-	$f_{IH} = 32 \text{ MHz}^{Note 3}$	Basic	$V_{DD} = 5.0 V$		2.3		mA
Current		mode	speed main) mode <sup>Note 5</sup>		operation	$V_{\text{DD}} = 3.0 \text{ V}$		2.3		mA
			mode		Normal	V <sub>DD</sub> = 5.0 V		5.2	8.5	mA
					operation	V <sub>DD</sub> = 3.0 V		5.2	8.5	mA
				fin = 24 MHz <sup>Note 3</sup>	Normal	V <sub>DD</sub> = 5.0 V		4.1	6.6	mA
					operation	V <sub>DD</sub> = 3.0 V		4.1	6.6	mA
				fiH = 16 MHz <sup>Note 3</sup> Norma	Normal	V <sub>DD</sub> = 5.0 V		3.0	4.7	mA
					operation	V <sub>DD</sub> = 3.0 V		3.0	4.7	mA
			LS (low- speed main) mode <sup>Note 5</sup>	f <sub>IH</sub> = 8 MHz <sup>№te 3</sup>	Normal	V <sub>DD</sub> = 3.0 V		1.3	2.1	mA
					operation	V <sub>DD</sub> = 2.0 V		1.3	2.1	mA
			LV (low- voltage main) mode Note 5	$f_{\text{IH}} = 4 \text{ MHz}^{\text{Note 3}}$	Normal	$V_{DD} = 3.0 V$		1.3	1.8	mA
					operation	V <sub>DD</sub> = 2.0 V		1.3	1.8	mA
			HS (high-	f <sub>MX</sub> = 20 MHz <sup>Note 2</sup> ,	Normal	Square wave input		3.4	5.5	mA
			speed main)	V <sub>DD</sub> = 5.0 V	operation	Resonator connection		3.6	5.7	mA
			mode Note 5	$f_{MX} = 20 \text{ MHz}^{Note 2},$	Normal	Square wave input		3.4	5.5	mA
				$V_{DD} = 3.0 V$	operation	Resonator connection		3.6	5.7	mA
				$f_{MX} = 10 \text{ MHz}^{Note 2},$	Normal	Square wave input		2.1	3.2	mA
				$V_{DD} = 5.0 V$	operation	Resonator connection		2.1	3.2	mA
				$f_{MX} = 10 \text{ MHz}^{Note 2},$	Normal operation	Square wave input		2.1	3.2	mA
				$V_{DD} = 3.0 V$		Resonator connection		2.1	3.2	mA
			LS (low- speed main) mode <sup>Note 5</sup>	$f_{MX} = 8 \text{ MHz}^{Note 2},$	Normal	Square wave input		1.2	2.0	mA
				$V_{DD} = 3.0 V$	operation	Resonator connection		1.2	2.0	mA
			mode	$f_{MX} = 8 \text{ MHz}^{Note 2},$	Normal	Square wave input		1.2	2.0	mA
				$V_{DD} = 2.0 V$	operation	Resonator connection		1.2	2.0	mA
			Subsystem	fsuв = 32.768 kHz	Normal	Square wave input		4.8	5.9	μA
			clock operation	Note 4 $T_A = -40^{\circ}C$	operation	Resonator connection		4.9	6.0	μA
				fsuв = 32.768 kHz	Normal	Square wave input		4.9	5.9	μA
				Note 4 $T_A = +25^{\circ}C$	operation	Resonator connection		5.0	6.0	μA
				fsuв = 32.768 kHz	Normal	Square wave input		5.0	7.6	μA
				Note 4	operation	Resonator connection		5.1	7.7	μA
				T <sub>A</sub> = +50°C fsub = 32.768 kHz	Normal	Square wave input		5.2	9.3	μA
				Note 4	operation	Resonator connection		5.3	9.3 9.4	μA
			_	$T_A = +70^{\circ}C$		Company to the state of		F 7	10.0	
				fsub = 32.768 kHz Note 4	Normal operation	Square wave input Resonator connection		5.7 5.8	13.3 13.4	μA μA
				T <sub>A</sub> = +85°C	.	TESUTIALUI CUTITIECUUT		5.0	13.4	μΑ

(Notes and Remarks are listed on the next page.)



## 2.4 AC Characteristics

# (TA = -40 to +85°C, 1.6 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Items	Symbol		Conditions	;	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсч	Main	HS (high-	$2.7V{\leq}V_{DD}{\leq}5.5V$	0.03125		1	μS
instruction execution time)		system clock (fmain)	speed main) mode	$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$	0.0625		1	μs
		operation	LS (low-speed main) mode	$1.8V\!\le\!V_{DD}\!\le\!5.5V$	0.125		1	μS
			LV (low- voltage main) mode	$1.6 V \le V_{DD} \le 5.5 V$	0.25		1	μS
		Subsystem of operation	clock (fsuв)	$1.8  V \! \le \! V_{DD} \! \le \! 5.5  V$	28.5	30.5	31.3	μS
		In the self	HS (high-	$2.7V{\leq}V_{\text{DD}}{\leq}5.5V$	0.03125		1	μS
		programming mode	speed main) mode	$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$	0.0625		1	μS
			LS (low-speed main) mode	$1.8V\!\leq\!V_{DD}\!\leq\!5.5V$	0.125		1	μS
			LV (low- voltage main) mode	$1.8 V \le V_{DD} \le 5.5 V$	0.25		1	μS
External system clock	fex	$2.7 \text{ V} \leq \text{V}_{DD} \leq$		1	1.0		20.0	MHz
frequency		2.4 V ≤ V <sub>DD</sub> <			1.0		16.0	MHz
		$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.4 \text{ V}$			1.0		8.0	MHz
		1.6 V ≤ V <sub>DD</sub> <	1.0		4.0	MHz		
	fexs				32		35	kHz
External system clock input	texh, texl	$2.7 \text{ V} \leq \text{V}_{DD} \leq$	< 5.5 V		24			ns
high-level width, low-level width		2.4 V ≤ V <sub>DD</sub> <			30			ns
		1.8 V ≤ V <sub>DD</sub> <			60			ns
		1.6 V ≤ V <sub>DD</sub> <			120			ns
	texns, texus				13.7			μS
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	tтıн, tтı∟				1/fмск+10			ns <sup>Note</sup>
TO00 to TO07, TO10 to TO17	fтo	HS (high-spe	eed 4.0 V	$\leq EV_{DD0} \leq 5.5 V$			16	MHz
output frequency		main) mode		$\leq$ EV <sub>DD0</sub> < 4.0 V			8	MHz
			1.8 V	$\leq$ EV <sub>DD0</sub> < 2.7 V			4	MHz
			1.6 V	≤ EV <sub>DD0</sub> < 1.8 V			2	MHz
		LS (low-spee	ed 1.8 V	$\leq EV_{DD0} \leq 5.5 V$			4	MHz
		main) mode	1.6 V	≤ EV <sub>DD0</sub> < 1.8 V			2	MHz
		LV (low-volta main) mode	age 1.6 V	$\leq EV_{\text{DD0}} \leq 5.5 \text{ V}$			2	MHz
PCLBUZ0, PCLBUZ1 output	<b>f</b> PCL	HS (high-spe	eed 4.0 V	$\leq EV_{DD0} \leq 5.5 V$			16	MHz
frequency		main) mode	2.7 V	$\leq EV_{DD0} < 4.0 V$			8	MHz
			1.8 V	$\leq$ EV <sub>DD0</sub> < 2.7 V			4	MHz
			1.6 V	$\leq EV_{DD0} < 1.8 V$			2	MHz
		LS (low-spee	ed 1.8 V	$\leq EV_{DD0} \leq 5.5 V$			4	MHz
		main) mode	1.6 V	$\leq EV_{DD0} < 1.8 V$			2	MHz
		LV (low-volta	age 1.8 V	$\leq EV_{\text{DD0}} \leq 5.5 \text{ V}$			4	MHz
		main) mode	1.6 V	$\leq$ EV <sub>DD0</sub> < 1.8 V			2	MHz
Interrupt input high-level width,	tintн,	INTP0	1.6 V	$\leq V_{\text{DD}} \leq 5.5 \text{ V}$	1			μS
low-level width	tintl	INTP1 to INT	[P11 1.6 V	$\leq EV_{DD0} \leq 5.5 V$	1			μS
Key interrupt input low-level	tкв	KR0 to KR7	1.8 V	$\leq EV_{DD0} \leq 5.5 V$	250			ns
width			1.6 V	$\leq EV_{DD0} < 1.8 V$	1			μS
RESET low-level width	trsl				10			μS

(Note and Remark are listed on the next page.)



(7)	Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp internal clock output,
	corresponding CSI00 only) (2/2)

Parameter	Symbol	mbol Conditions HS (high-speed LS (low-speed main) Mode main) Mode		•	LV (low main)	Unit			
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) <sup>Note 2</sup>	tsikı	$\label{eq:states} \begin{split} 4.0 \ V &\leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \end{split}$	23		110		110		ns
		$C_{b}=20 \text{ pF},  \text{R}_{b}=1.4  \text{k}\Omega$							
		$\label{eq:V} \begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 4.0 \ V, \\ 2.3 \ V \leq V_{\text{b}} \leq 2.7 \ V, \end{array}$	33		110		110		ns
		$C_{b}=20 \text{ pF},  \text{R}_{b}=2.7  \text{k}\Omega$							
SIp hold time (from SCKp↓) <sup>№te 2</sup>	tksi1	$\begin{array}{l} 4.0 \; V \leq E V_{\text{DD0}} \leq 5.5 \; V, \\ 2.7 \; V \leq V_{\text{b}} \leq 4.0 \; V, \end{array}$	10		10		10		ns
		$C_{b}=20 \text{ pF},  \text{R}_{b}=1.4  \text{k}\Omega$							
		$\label{eq:V_def} \begin{split} 2.7 \ V &\leq E V_{\text{DD0}} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \end{split}$	10		10		10		ns
		$C_{b}=20 \text{ pF},  \text{R}_{b}=2.7  \text{k}\Omega$							
Delay time from SCKp↑ to	tkso1	$\label{eq:V_decomposition} \begin{split} 4.0 \ V &\leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_{\text{b}} \leq 4.0 \ V, \end{split}$		10		10		10	ns
SOp output Note 2		$C_{b}=20 \text{ pF},  \text{R}_{b}=1.4  \text{k}\Omega$							
		$\label{eq:V_def} \begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \end{array}$		10		10		10	ns
		$C_{b}=20 \text{ pF},  \text{R}_{b}=2.7  \text{k}\Omega$							

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ 

**Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V<sub>DD</sub> tolerance (When 20- to 52-pin products)/EV<sub>DD</sub> tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V<sub>IH</sub> and V<sub>IL</sub>, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** R<sub>b</sub>[Ω]:Communication line (SCKp, SOp) pull-up resistance, C<sub>b</sub>[F]: Communication line (SCKp, SOp) load capacitance, V<sub>b</sub>[V]: Communication line voltage
  - p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
    g: PIM and POM number (g = 1)
  - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

- n: Channel number (mn = 00))
- 4. This value is valid only when CSI00's peripheral I/O redirect function is not used.



**Notes 1.** The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

- Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode:  $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ 

<R>



## 2.6 Analog Characteristics

## 2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
	Reference voltage (+) = AVREFP	Reference voltage (+) = VDD	Reference voltage (+) = VBGR
Input channel	Reference voltage (-) = AVREFM	Reference voltage (-) = Vss	Reference voltage (-) = AVREFM
ANI0 to ANI14	Refer to <b>2.6.1 (1)</b> .	Refer to 2.6.1 (3).	Refer to <b>2.6.1 (4)</b> .
ANI16 to ANI26	Refer to <b>2.6.1 (2)</b> .		
Internal reference voltage	Refer to <b>2.6.1 (1)</b> .		_
Temperature sensor output			
voltage			

(1) When reference voltage (+)= AV<sub>REFP</sub>/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV<sub>REFM</sub>/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(T<sub>A</sub> = -40 to +85°C, 1.6 V  $\leq$  AV<sub>REFP</sub>  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V, V<sub>SS</sub> = 0 V, Reference voltage (+) = AV<sub>REFP</sub>, Reference voltage (-) = AV<sub>REFM</sub> = 0 V)

Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error <sup>Note 1</sup>	AINL	10-bit resolution	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$		1.2	±3.5	LSB
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$		1.2	±7.0	LSB
Conversion time	<b>t</b> CONV	10-bit resolution	$3.6~V \leq V \text{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI2 to	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.1875		39	μS
		ANI14	$1.8~V \leq V \text{DD} \leq 5.5~V$	17		39	μS
			$1.6~V \leq V \text{DD} \leq 5.5~V$	57		95	μS
		10-bit resolution Target pin: Internal	$3.6~V \leq V \text{DD} \leq 5.5~V$	2.375		39	μS
			$2.7~V \leq V \text{DD} \leq 5.5~V$	3.5625		39	μS
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
Zero-scale error <sup>Notes 1, 2</sup>	Ezs	10-bit resolution	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±0.25	%FSR
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±0.50	%FSR
Full-scale error <sup>Notes 1, 2</sup>	Ers	10-bit resolution	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±0.25	%FSR
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±0.50	%FSR
Integral linearity error <sup>Note 1</sup>	ILE	10-bit resolution	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±2.5	LSB
		$AV_{REFP} = V_{DD}{}^{Note 3}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±5.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±1.5	LSB
		$AV_{REFP} = V_{DD}{}^{Note 3}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±2.0	LSB
Analog input voltage	VAIN	ANI2 to ANI14		0		AVREFP	V
		Internal reference voltage (2.4 V $\leq$ V <sub>DD</sub> $\leq$ 5.5 V, HS		VBGR Note 5			V
		Temperature sensor outp (2.4 V $\leq$ VDD $\leq$ 5.5 V, HS	0	VTMPS25 Note 5		5	V

(Notes are listed on the next page.)



# (2) When reference voltage (+) = AV<sub>REFP</sub>/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV<sub>REFM</sub>/ANI1 (ADREFM = 1), target pin : ANI16 to ANI26

$(T_{A} = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V},$
Reference voltage (+) = AVREFP, Reference voltage (–) = AVREFM = 0 V)

Parameter	Symbol	Condit	ions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error <sup>Note 1</sup>	AINL	10-bit resolution $EV_{DD0} = AV_{REFP} = V_{DD}^{Notes 3, 4}$	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$		1.2	±5.0	LSB
			$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$		1.2	±8.5	LSB
Conversion time	<b>t</b> CONV	10-bit resolution	$3.6~V \le V \text{DD} \le 5.5~V$	2.125		39	μs
		Target ANI pin : ANI16 to	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.1875		39	μS
		ANI26	$1.8~V \leq V \text{DD} \leq 5.5~V$	17		39	μs
			$1.6~V \leq V \text{DD} \leq 5.5~V$	57		95	μS
Zero-scale error <sup>Notes 1, 2</sup>	L23	10-bit resolution EVDD0 = AV <sub>REFP</sub> = V <sub>DD</sub> <sup>Notes 3, 4</sup>	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±0.35	%FSR
			$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note}}$			±0.60	%FSR
Full-scale error <sup>Notes 1, 2</sup>	Efs	10-bit resolution EVDD0 = $AV_{REFP} = V_{DD}^{Notes 3, 4}$	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±0.35	%FSR
			$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±0.60	%FSR
Integral linearity error <sup>Note</sup>	ILE	10-bit resolution	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±3.5	LSB
1		$EVDD0 = AV_{REFP} = V_{DD}^{Notes 3, 4}$	$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±6.0	LSB
Differential linearity	DLE	10-bit resolution	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±2.0	LSB
error <sup>Note 1</sup>	$EVDD0 = AV_REFP = V_DD^{Notes 3, 4}$	$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±2.5	LSB	
Analog input voltage	VAIN	ANI16 to ANI26	·	0		AVREFP and EVDD0	V

**Notes 1.** Excludes quantization error ( $\pm 1/2$  LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When AV<sub>REFP</sub> < V<sub>DD</sub>, the MAX. values are as follows. Overall error: Add  $\pm 1.0$  LSB to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>. Zero-scale error/Full-scale error: Add  $\pm 0.05\%$ FSR to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>. Integral linearity error/ Differential linearity error: Add  $\pm 0.5$  LSB to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>.
- 4. When AV<sub>REFP</sub> < EV<sub>DD0</sub> ≤ V<sub>DD</sub>, the MAX. values are as follows. Overall error: Add ±4.0 LSB to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>. Zero-scale error/Full-scale error: Add ±0.20%FSR to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>. Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>.
- 5. When the conversion time is set to 57  $\mu$ s (min.) and 95  $\mu$ s (max.).



(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

$(T_{A} = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \leq \text{EV}_{\text{DD}} = \text{EV}_{\text{DD}} \leq 5.5 \text{ V}, \text{ Vss} = \text{EV}_{\text{SS}} = \text{EV}_{\text{SS}} = 0 \text{ V}, \text{ Reference voltage (+)} = \text{V}_{\text{DD}}, \text{ V}_{\text{DD}} = 0 \text{ V}, \text{ Reference voltage (+)} = 0 \text{ V},  Reference voltage (+)$
Reference voltage (-) = Vss)

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit	
Overall error <sup>Note 1</sup>	AINL	10-bit resolution	$1.8~V \le V \text{DD} \le 5.5~V$		1.2	±7.0	LSB
			$\frac{1.6~V \leq V\text{DD} \leq 5.5~V}{_{\text{Note 3}}}$		1.2	±10.5	LSB
Conversion time	tconv	CONV 10-bit resolution	$3.6~V \le V \text{DD} \le 5.5~V$	2.125		39	μs
		Target pin: ANI0 to ANI14,	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.1875		39	μs
		ANI16 to ANI26	$1.8~V \leq V \text{DD} \leq 5.5~V$	17		39	μs
			$1.6~V \leq V \text{DD} \leq 5.5~V$	57		95	μs
Conversion time	<b>t</b> CONV	10-bit resolution	$3.6~V \leq V \text{DD} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.5625		39	μs
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
Zero-scale error <sup>Notes 1, 2</sup>	Ezs	10-bit resolution	$1.8~V \le V \text{DD} \le 5.5~V$			±0.60	%FSR
			$1.6~V \leq V \text{DD} \leq 5.5~V$ Note 3			±0.85	%FSR
Full-scale error <sup>Notes 1, 2</sup>	Efs	E <sub>FS</sub> 10-bit resolution	$1.8~V \le V \text{DD} \le 5.5~V$			±0.60	%FSR
			$1.6~V \leq V \text{DD} \leq 5.5~V$ Note 3			±0.85	%FSR
Integral linearity error <sup>Note 1</sup>	ILE	10-bit resolution	$1.8~V \leq V \text{DD} \leq 5.5~V$			±4.0	LSB
			$1.6~V \leq V \text{DD} \leq 5.5~V$ Note 3			±6.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$1.8~V \leq V \text{DD} \leq 5.5~V$			±2.0	LSB
			$\frac{1.6~V \leq V\text{DD} \leq 5.5~V}{_{\text{Note 3}}}$			±2.5	LSB
Analog input voltage	VAIN	ANI0 to ANI14		0		Vdd	V
		ANI16 to ANI26		0		EVDD0	V
		Internal reference voltage (2.4 V $\leq$ VDD $\leq$ 5.5 V, HS (high-speed main) mode)			VBGR Note 4		V
		Temperature sensor output (2.4 V $\leq$ V <sub>DD</sub> $\leq$ 5.5 V, HS (high	•	VTMPS25 Note 4			V

Notes 1. Excludes quantization error ( $\pm 1/2$  LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When the conversion time is set to 57  $\mu s$  (min.) and 95  $\mu s$  (max.).
- 4. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.



#### RL78/G13 3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS TA = -40 to +105°C)

Remark The electrical characteristics of the products G: Industrial applications (T<sub>A</sub> = -40 to +105°C) are different from those of the products "A: Consumer applications, and D: Industrial applications". For details, refer to 3.1 to 3.10.

#### 3.1 Absolute Maximum Ratings

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	VDD		–0.5 to +6.5	V
	EVDD0, EVDD1	EVDD0 = EVDD1	–0.5 to +6.5	V
	EVsso, EVss1	EVsso = EVss1	–0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	$-0.3$ to +2.8 and $-0.3$ to $V_{\text{DD}}$ +0.3 $^{\text{Note 1}}$	V
Input voltage	VI1	P00 to P07, P10 to P17, P30 to P37, P40 to P47,	-0.3 to EV <sub>DD0</sub> +0.3	V
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	and –0.3 to $V_{DD}$ +0.3 <sup>Note 2</sup>	
	V <sub>I2</sub>	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V <sub>DD</sub> +0.3 <sup>Note 2</sup>	V
Output voltage	Voi	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147		V
	V <sub>02</sub>	P20 to P27, P150 to P156	-0.3 to V <sub>DD</sub> +0.3 <sup>Note 2</sup>	V
Analog input voltage	VAI1	ANI16 to ANI26	$-0.3$ to EV_DD0 +0.3 and $-0.3$ to AV_{REF}(+) +0.3 $^{\text{Notes 2, 3}}$	V
	Vai2	ANI0 to ANI14	$-0.3$ to V_DD +0.3 and $-0.3$ to AV_{REF}(+) +0.3^{Notes 2,3}	V

#### Absolute Maximum Ratings (T<sub>A</sub> = 25°C) (1/2)

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
  - 2. Must be 6.5 V or lower.
  - **3.** Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
  - **2.**  $AV_{REF}(+)$  : + side reference voltage of the A/D converter.
  - **3.** Vss : Reference voltage



Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іонт	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins –170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	IOL1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	IOL2	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operati	on mode	-40 to +105	°C
temperature		In flash memory	programming mode		
Storage temperature	Tstg			-65 to +150	°C

#### Absolute Maximum Ratings (TA = 25°C) (2/2)

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



#### 3.3 DC Characteristics

#### 3.3.1 Pin characteristics

#### $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (1/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high <sup>∾te 1</sup>	Іон1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$2.4~V \leq EV_{DD0} \leq 5.5~V$			-3.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37,	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$			-30.0	mA
		P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			-10.0	mA
		$(\text{When duty} \le 70\%^{\text{Note 3}})$	$2.4~V \leq EV_{\text{DD0}} < 2.7~V$			-5.0	mA
		Total of P05, P06, P10 to P17, P30, P31,				-30.0	mA
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to	$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			-19.0	mA
		P117, P146, P147 (When duty $\leq 70\%^{\text{Note 3}}$ )	$2.4~V \leq EV_{DD0} < 2.7~V$			-10.0	mA
		Total of all pins (When duty ≤ 70% <sup>№te 3</sup> )	$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V$			-60.0	mA
	Іон2	Per pin for P20 to P27, P150 to P156	2,4 V $\leq$ V_{DD} $\leq$ 5.5 V			-0.1 <sup>Note 2</sup>	mA
		Total of all pins (When duty $\leq 70\%^{Note 3}$ )	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV<sub>DD0</sub>, EV<sub>DD1</sub>, V<sub>DD</sub> pins to an output pin.
  - 2. Do not exceed the total current value.
  - 3. Specification under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).
    - Total output current of pins =  $(I_{OH} \times 0.7)/(n \times 0.01)$ 
      - <Example> Where n = 80% and  $I_{OH} = -10.0 \text{ mA}$ 
        - Total output current of pins =  $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$  mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



## 3.3.2 Supply current characteristics

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit									
Supply	IDD1	Operating	HS (high-	$f_{IH}=32~MHz^{Note~3}$	Basic	$V_{DD} = 5.0 V$		2.1		mA									
Current Note 1	nt mode	mode speed main) mode <sup>Note 5</sup>		operatio n	V <sub>DD</sub> = 3.0 V		2.1		mA										
					Normal	$V_{DD} = 5.0 V$		4.6	7.5	mA									
					operatio n	$V_{DD} = 3.0 V$		4.6	7.5	mA									
				$f_{IH} = 24 \text{ MHz}^{Note 3}$	Normal	$V_{DD} = 5.0 V$		3.7	5.8	mA									
					operatio n	V <sub>DD</sub> = 3.0 V		3.7	5.8	mA									
				$f_{IH} = 16 \text{ MHz}^{Note 3}$	Normal	$V_{DD} = 5.0 V$		2.7	4.2	mA									
					operatio n	V <sub>DD</sub> = 3.0 V		2.7	4.2	mA									
			HS (high-	$f_{MX} = 20 \text{ MHz}^{Note 2},$	Normal	Square wave input		3.0	4.9	mA									
			speed main) mode <sup>№ote 5</sup>	$V_{DD} = 5.0 V$	operatio n	Resonator connection		3.2	5.0	mA									
				$f_{MX} = 20 \text{ MHz}^{Note 2},$	Normal	Square wave input		3.0	4.9	mA									
				$V_{DD} = 3.0 V$	operatio n	Resonator connection		3.2	5.0	mA									
		Subsystem			$f_{MX} = 10 \text{ MHz}^{Note 2},$	Normal	Square wave input		1.9	2.9	mA								
				VDD - 3.0 V	operatio n	Resonator connection		1.9	2.9	mA									
								-	$f_{MX} = 10 \text{ MHz}^{Note 2},$	Normal	Square wave input		1.9	2.9	mA				
										$V_{DD} = 3.0 V$	operatio n	Resonator connection		1.9	2.9	mA			
						Subsystem	fsub = 32.768 kHz Normal	Square wave input		4.1	4.9	μA							
			clock operation		n	Resonator connection		4.2	5.0	μA									
				fsuв = 32.768 kHz	Normal	Square wave input		4.1	4.9	μA									
													Note 4 $T_A = +25^{\circ}C$	operatio n	Resonator connection		4.2	5.0	μA
						fsuв = 32.768 kHz	Normal	Square wave input		4.2	5.5	μA							
						Note 4 $T_A = +50^{\circ}C$	operatio n	Resonator connection		4.3	5.6	μA							
				fsuв = 32.768 kHz	Normal	Square wave input		4.3	6.3	μA									
					Note 4	operatio n	Resonator connection		4.4	6.4	μA								
					$T_A = +70^{\circ}C$	Nema			4.0	~ ~									
						fsub = 32.768 kHz Note 4	Normal operation	Square wave input		4.6	7.7	μA							
					T <sub>A</sub> = +85°C	operation	Resonator connection		4.7	7.8	μA								
				fsuв = 32.768 kHz	Normal	Square wave input		6.9	19.7	μA									
				<sub>Note 4</sub> T <sub>A</sub> = +105°C	operation	Resonator connection		7.0	19.8	μA									

#### (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (TA = -40 to $+105^{\circ}$ C, 2.4 V $\leq EV_{DD0} \leq V_{DD} \leq 5.5$ V, Vss = EVss<sub>0</sub> = 0 V) (1/2)

(Notes and Remarks are listed on the next page.)



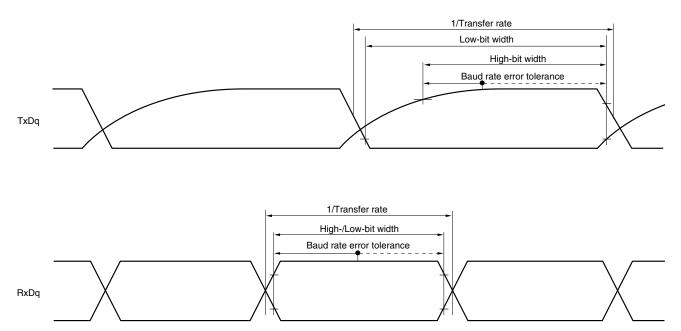
Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	IFIL Note 1				0.20		μA
RTC operating current	RTC Notes 1, 2, 3				0.02		μA
12-bit interval timer operating current	IT Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	WDT Notes 1, 2, 5	f⊩ = 15 kHz			0.22		μA
A/D converter	ADC Notes 1, 6	When conversion	Normal mode, $AV_{REFP} = V_{DD} = 5.0 V$		1.3	1.7	mA
operating current	Notes 1, 6	at maximum speed	Low voltage mode, $AV_{REFP} = V_{DD} = 3.0 V$		0.5	0.7	mA
A/D converter reference voltage current	ADREF Note 1				75.0		μA
Temperature sensor operating current	ITMPS Note 1				75.0		μA
LVD operating current	ILVD Notes 1, 7				0.08		μA
Self programming operating current	FSP Notes 1, 9				2.50	12.20	mA
BGO operating current	BGO Notes 1, 8				2.50	12.20	mA
SNOOZE	Isnoz	ADC operation	The mode is performed Note 10		0.50	1.10	mA
operating current	Note 1		The A/D conversion operations are performed, Loe voltage mode, $AV_{REFP} = V_{DD} = 3.0 V$		1.20	2.04	mA
		CSI/UART operation	on		0.70	1.54	mA

#### (3) Peripheral Functions (Common to all products) (TA = -40 to $+105^{\circ}$ C, 2.4 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

**Notes 1.** Current flowing to the VDD.

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed onchip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates.





UART mode bit width (during communication at different potential) (reference)

 Remarks 1.
 Rb[Ω]:Communication line (TxDq) pull-up resistance,

 Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage

- **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
- 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

**4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.



Parameter	Symbol	Symbol Conditions		HS (high-speed main) Mode		
			MIN.	MAX.		
SIp setup time (to SCKp↓) <sup>№te</sup>	tsik1	$4.0 \ V \leq EV_{\text{DD}} \leq 5.5 \ V, \ 2.7 \ V \leq V_{\text{b}} \leq 4.0 \ V,$	88		ns	
		$C_b = 30 \text{ pF}, \text{ R}_b = 1.4 \text{ k}\Omega$				
		$2.7 \text{ V} \le EV_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$	88		ns	
		$C_b$ = 30 pF, $R_b$ = 2.7 k $\Omega$				
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$	220		ns	
		$C_b = 30 \text{ pF},  \text{R}_b = 5.5  \text{k}\Omega$				
SIp hold time (from SCKp↓) <sup>№te</sup>	tksi1	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$	38		ns	
		$C_b = 30 \text{ pF}, \text{ R}_b = 1.4 \text{ k}\Omega$				
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	38		ns	
		$C_b = 30 \text{ pF},  \text{R}_b = 2.7  \text{k}\Omega$				
		$2.4 \ V \leq EV_{\text{DD0}} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$	38		ns	
		$C_b = 30 \text{ pF},  \text{R}_b = 5.5  \text{k}\Omega$				
Delay time from SCKp↑ to	tkso1	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$		50	ns	
SOp output <sup>Note</sup>		$C_b = 30 \text{ pF},  \text{R}_b = 1.4  \text{k}\Omega$				
		$2.7 \ V \leq EV_{\text{DD0}} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$		50	ns	
		$C_b$ = 30 pF, $R_b$ = 2.7 k $\Omega$				
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$		50	ns	
		$C_{b} = 30 \text{ pF}, R_{b} = 5.5 \text{ k}\Omega$				

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

**Note** When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V<sub>DD</sub> tolerance (for the 20- to 52-pin products)/EV<sub>DD</sub> tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V<sub>IH</sub> and V<sub>IL</sub>, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

